

Digital Transistors (BRT)

R₁ = 22 kΩ, R₂ = 22 kΩ

NPN Transistors with Monolithic Bias Resistor Network

MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

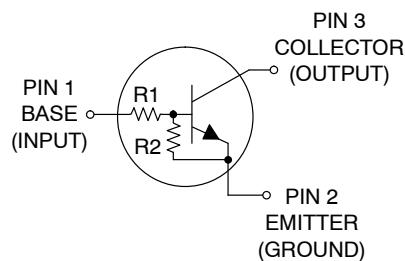
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_A = 25 °C)

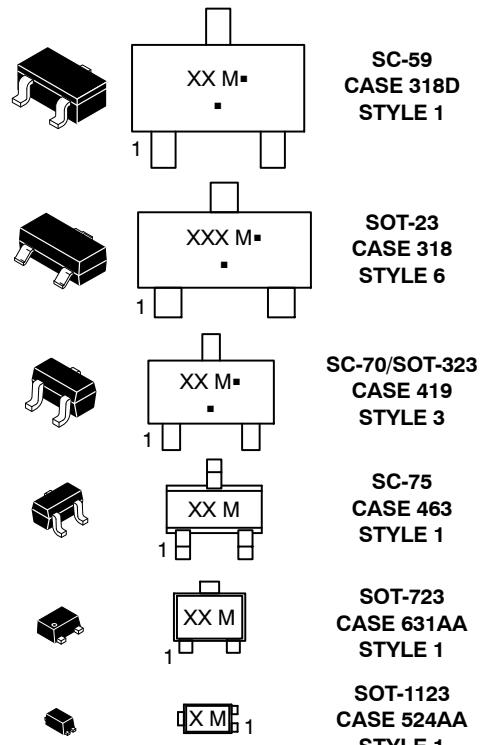
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	I _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	40	Vdc
Input Reverse Voltage	V _{IN(rev)}	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

PIN CONNECTIONS



MARKING DIAGRAMS



XXX = Specific Device Code

M = Date Code*

▪ = Pb-Free Package

(Note: Microdot may be in either location)

* Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2212T1G, NSVMUN2212T1G*	8B	SC-59 (P-Free)	3000 / Tape & Reel
MMUN2212LT1G, NSVMMUN2212LT1G*	A8B	SOT-23 (P-Free)	3000 / Tape & Reel
MUN5212T1G, SMUN5212T1G*	8B	SC-70/SOT-323 (P-Free)	3000 / Tape & Reel
DTC124EET1G, SDTC124EET1G*	8B	SC-75 (P-Free)	3000 / Tape & Reel
DTC124EM3T5G	8B	SOT-723 (P-Free)	8000 / Tape & Reel
NSBC124EF3T5G	L	SOT-1123 (P-Free)	8000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

* S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

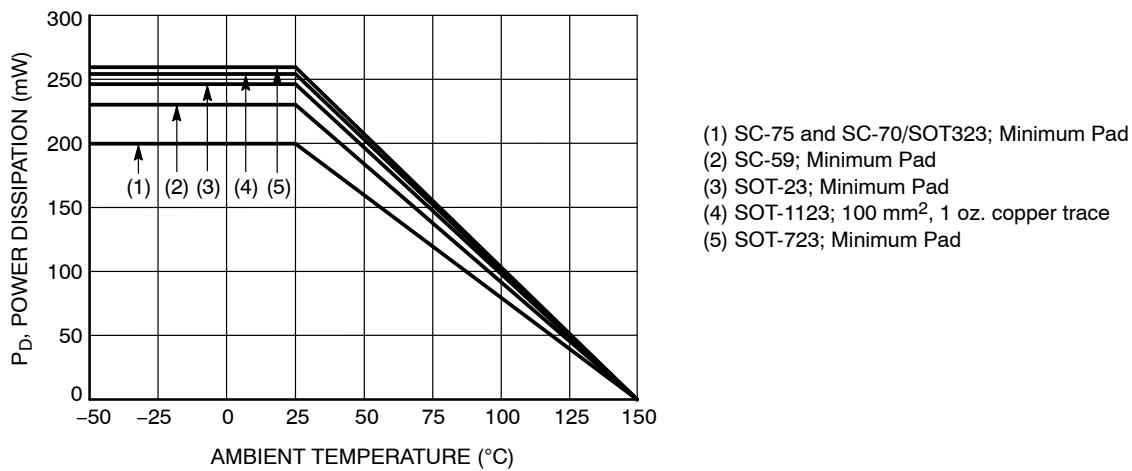


Figure 1. Derating Curve

MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2212)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	230 338 1.8 2.7	mW mW/ $^\circ\text{C}$
Derate above 25 $^\circ\text{C}$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	540 370	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	264 287	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-23) (MMUN2212L)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	246 400 2.0 3.2	mW mW/ $^\circ\text{C}$
Derate above 25 $^\circ\text{C}$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	508 311	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	174 208	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5212)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	202 310 1.6 2.5	mW mW/ $^\circ\text{C}$
Derate above 25 $^\circ\text{C}$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	618 403	$^\circ\text{C/W}$
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	280 332	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SC-75) (DTC124EE)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	200 300 1.6 2.4	mW mW/ $^\circ\text{C}$
Derate above 25 $^\circ\text{C}$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	600 400	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS (SOT-723) (DTC124EM3)			
Total Device Dissipation $T_A = 25^\circ\text{C}$	P_D	260 600 2.0 4.8	mW mW/ $^\circ\text{C}$
Derate above 25 $^\circ\text{C}$			
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	480 205	$^\circ\text{C/W}$

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm², 1 oz. copper traces, still air.
4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-723) (DTC124EM3)			
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-1123) (NSBC124EF3)			
Total Device Dissipation T _A = 25 °C Derate above 25 °C	(Note 3) (Note 4) (Note 3) (Note 4)	P _D	254 297 2.0 2.4
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	R _{θJA}	493 421
Thermal Resistance, Junction to Lead	(Note 3)	R _{θJL}	193
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm², 1 oz. copper traces, still air.
4. FR-4 @ 500 mm², 1 oz. copper traces, still air.

Table 3. ELECTRICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}	–	–	0.2	mAdc
Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 5) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	–	–	Vdc

ON CHARACTERISTICS

DC Current Gain (Note 5) (I _C = 5.0 mA, V _{CE} = 10 V)	h _{FE}	60	100	–	
Collector-Emitter Saturation Voltage (Note 5) (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}	–	–	0.25	Vdc
Input Voltage (off) (V _{CE} = 5.0 V, I _C = 100 μA)	V _{i(off)}	–	1.2	0.8	Vdc
Input Voltage (on) (V _{CE} = 0.3 V, I _C = 5.0 mA)	V _{i(on)}	2.5	1.6	–	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 kΩ)	V _{OL}	–	–	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 kΩ)	V _{OH}	4.9	–	–	Vdc
Input Resistor	R ₁	15.4	22	28.6	kΩ
Resistor Ratio	R ₁ /R ₂	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS
MUN2212, MMUN2212L, NSVMUN2212LT1G, MUN5212, DTC124EE, DTC124EM3

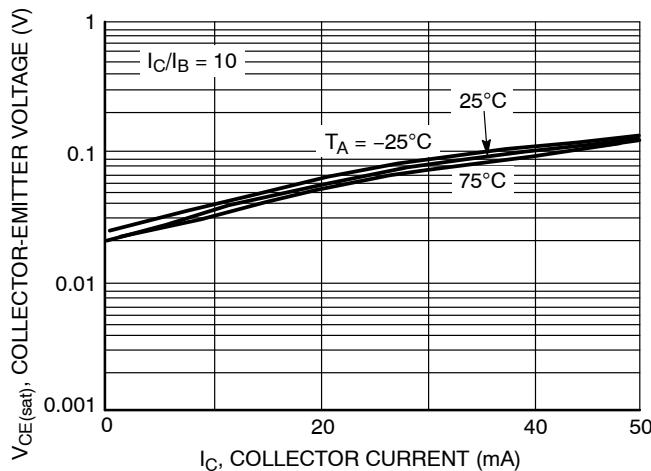


Figure 2. $V_{CE(sat)}$ vs. I_C

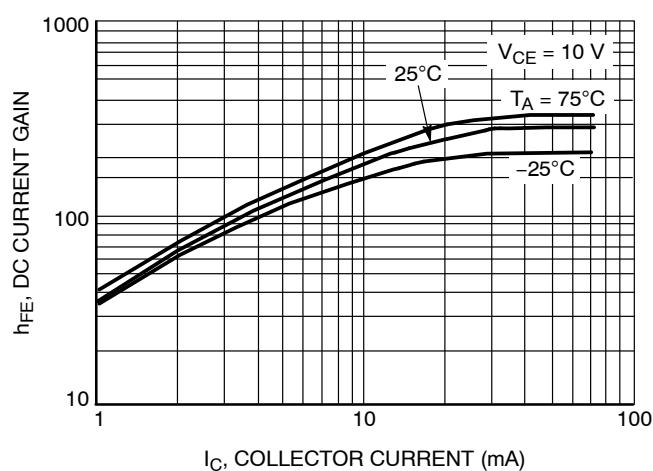


Figure 3. DC Current Gain

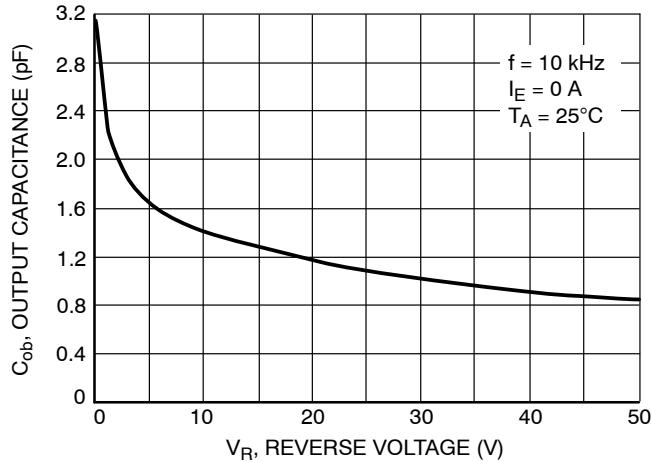


Figure 4. Output Capacitance

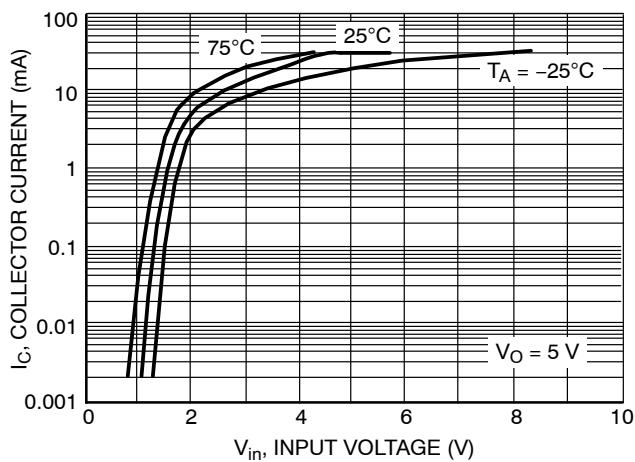


Figure 5. Output Current vs. Input Voltage

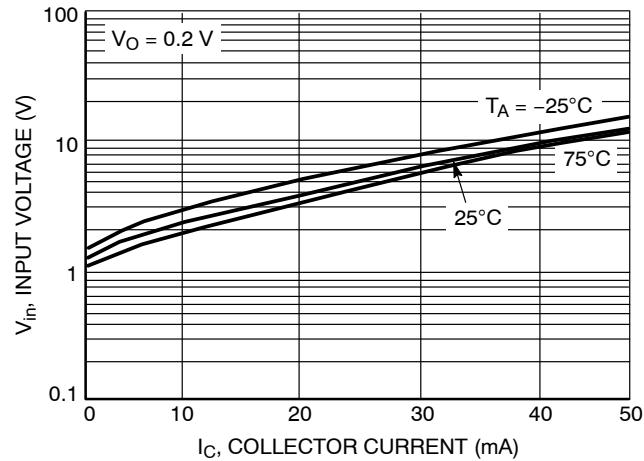


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NSBC124EF3

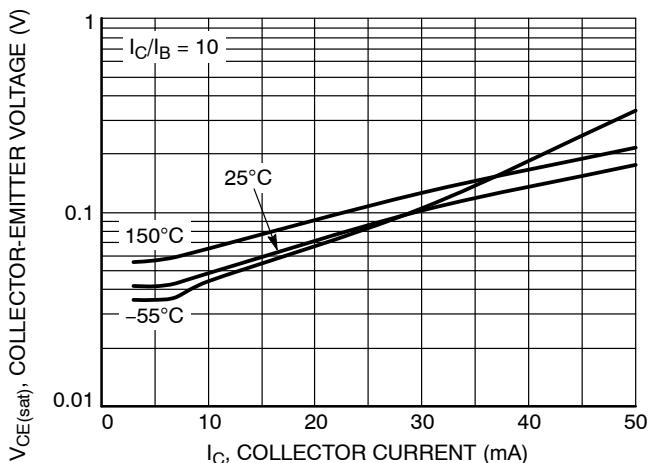


Figure 7. $V_{CE(sat)}$ vs. I_C

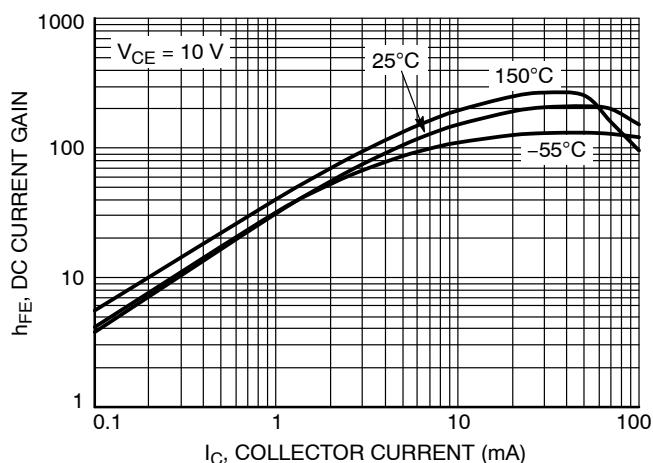


Figure 8. DC Current Gain

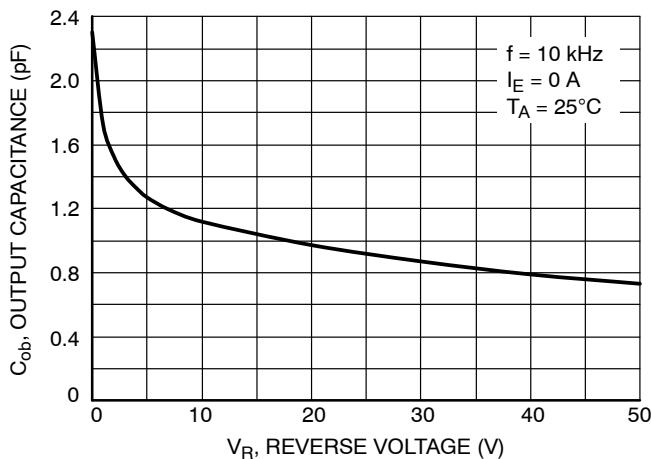


Figure 9. Output Capacitance

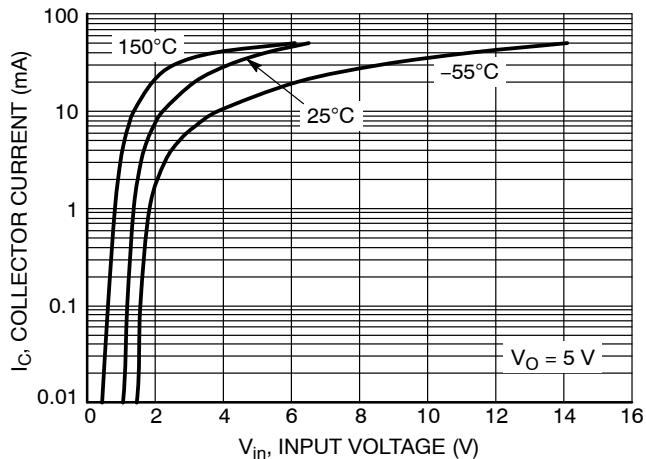


Figure 10. Output Current vs. Input Voltage

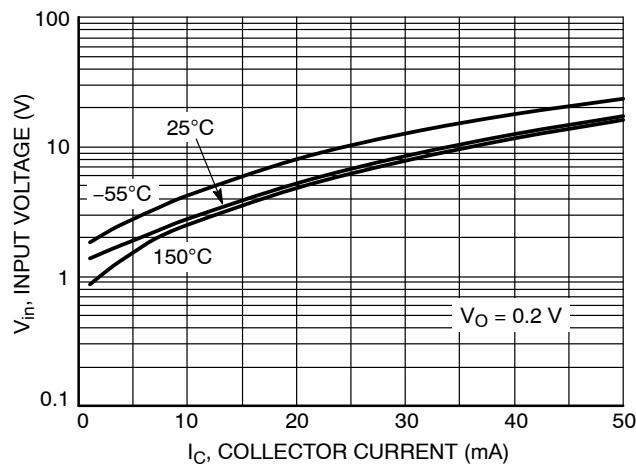


Figure 11. Input Voltage vs. Output Current

REVISION HISTORY

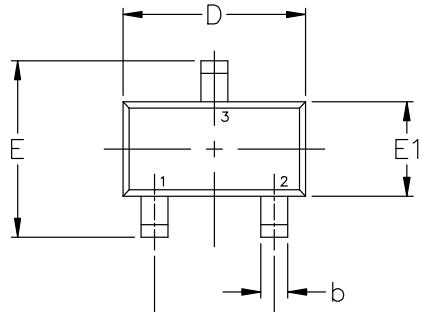
Revision	Description of Changes	Date
4	Rebranded the Data Sheet to onsemi format.	06/19/2025

PACKAGE DIMENSIONS

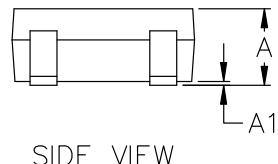


SC-59-3 2.90x1.50x1.15, 1.90P
CASE 318D
ISSUE J

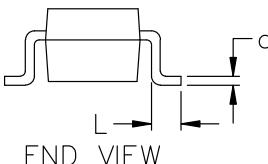
DATE 15 FEB 2024



TOP VIEW



SIDE VIEW

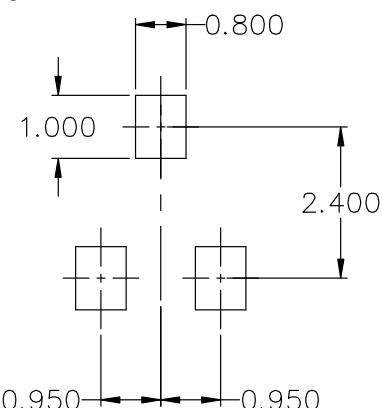


END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

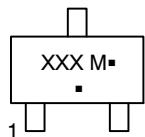
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.00	1.15	1.30
A1	0.01	0.06	0.10
b	0.35	0.43	0.50
c	0.09	0.14	0.18
D	2.70	2.90	3.10
E	2.50	2.80	3.00
E1	1.30	1.50	1.70
e	1.90 BSC		
L	0.20	0.40	0.60



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SODERRM/D.

**GENERIC
MARKING DIAGRAM***



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package*

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

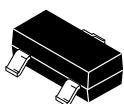
STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. N.C.
3. ANODE

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE

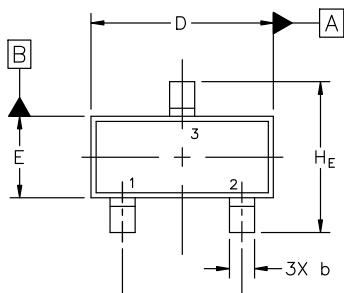
STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE/CATHODE



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

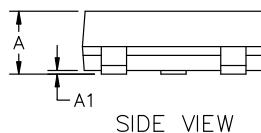
DATE 14 AUG 2024



TOP VIEW

DETAIL "A"

Scale 3:1

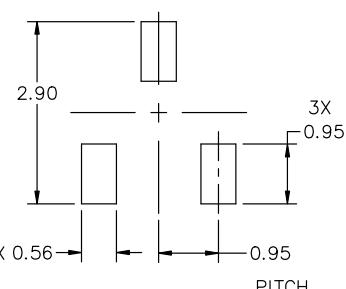
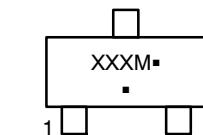


SIDE VIEW

DETAIL "A"

END VIEW

SEATING PLANE

GENERIC
MARKING DIAGRAM*

XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

MILLIMETERS

DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 1 OF 2

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SOT-23 (TO-236) 2.90x1.30x1.00 1.90P

CASE 318

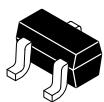
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5:
CANCELLEDSTYLE 6:
PIN 1. BASE
2. Emitter
3. CollectorSTYLE 7:
PIN 1. Emitter
2. Base
3. CollectorSTYLE 8:
PIN 1. Anode
2. No Connection
3. CathodeSTYLE 9:
PIN 1. Anode
2. Anode
3. CathodeSTYLE 10:
PIN 1. Drain
2. Source
3. GateSTYLE 11:
PIN 1. Anode
2. Cathode
3. Cathode-AnodeSTYLE 12:
PIN 1. Cathode
2. Cathode
3. AnodeSTYLE 13:
PIN 1. Source
2. Drain
3. GateSTYLE 14:
PIN 1. Cathode
2. Gate
3. AnodeSTYLE 15:
PIN 1. Gate
2. Cathode
3. AnodeSTYLE 16:
PIN 1. Anode
2. Cathode
3. CathodeSTYLE 17:
PIN 1. No Connection
2. Anode
3. CathodeSTYLE 18:
PIN 1. No Connection
2. Cathode
3. AnodeSTYLE 19:
PIN 1. Cathode
2. Anode
3. Cathode-AnodeSTYLE 20:
PIN 1. Cathode
2. Anode
3. GateSTYLE 21:
PIN 1. Gate
2. Source
3. DrainSTYLE 22:
PIN 1. Return
2. Output
3. InputSTYLE 23:
PIN 1. Anode
2. Anode
3. CathodeSTYLE 24:
PIN 1. Gate
2. Drain
3. SourceSTYLE 25:
PIN 1. Anode
2. Cathode
3. GateSTYLE 26:
PIN 1. Cathode
2. Anode
3. No ConnectionSTYLE 27:
PIN 1. Cathode
2. Cathode
3. CathodeSTYLE 28:
PIN 1. Anode
2. Anode
3. Anode

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DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 2 OF 2

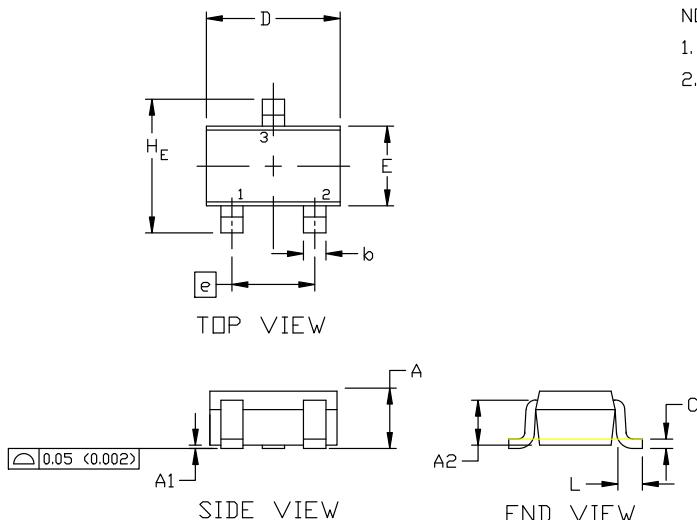
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SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

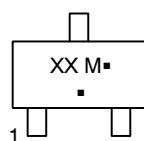
DATE 11 OCT 2022



NOTES:

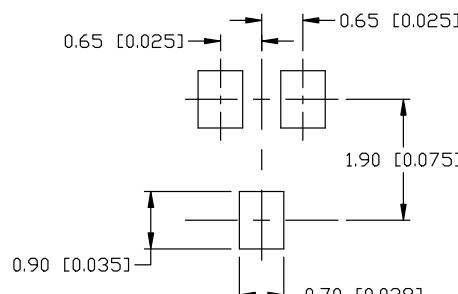
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM

XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



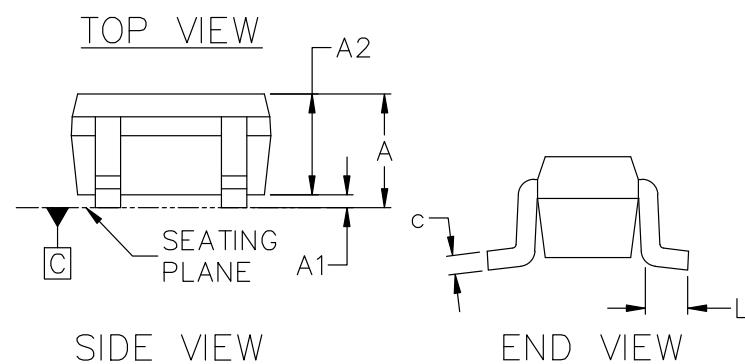
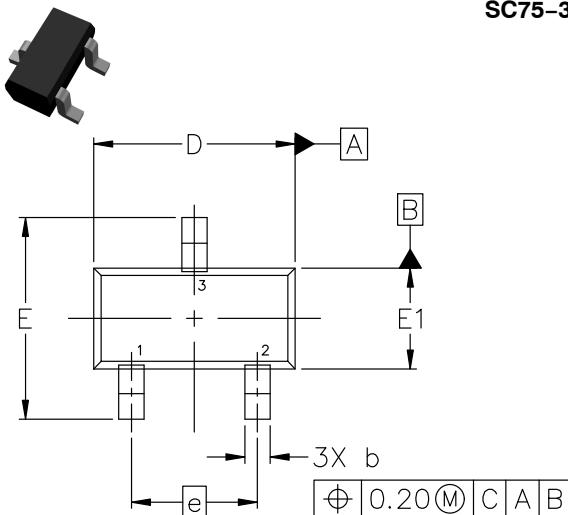
* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. Emitter 3. Collector	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE
STYLE 6: PIN 1. Emitter 2. BASE 3. COLLECTOR	STYLE 7: PIN 1. BASE 2. Emitter 3. COLLECTOR	STYLE 8: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 9: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. ANODE-CATHODE
				STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE

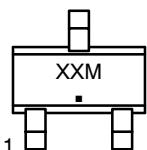
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DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

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SIDE VIEW

END VIEW

GENERIC
MARKING DIAGRAM*

XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

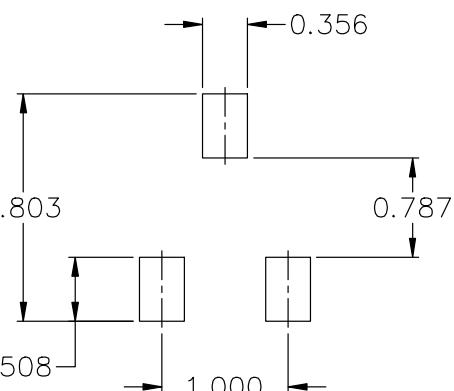
STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

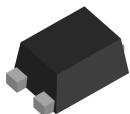


RECOMMENDED MOUNTING FOOTPRINT*

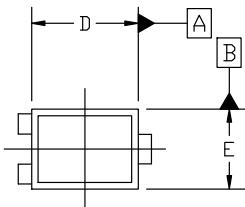
* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

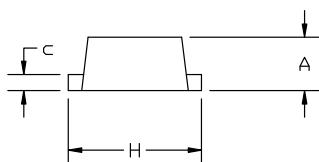
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SOT-1123 0.80x0.60x0.37, 0.35P
CASE 524AA
ISSUE D

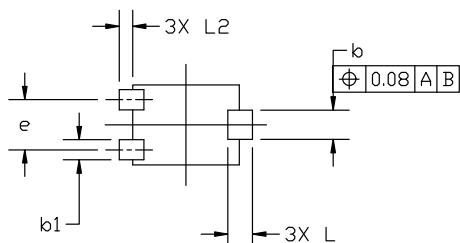
DATE 18 JAN 2024



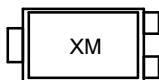
TOP VIEW



SIDE VIEW



BOTTOM VIEW

**GENERIC
MARKING DIAGRAM***


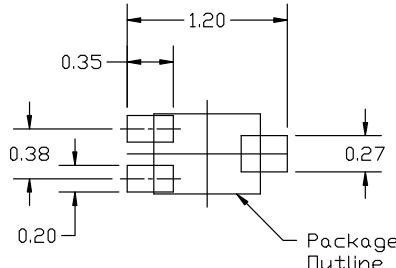
X = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.15	0.22	0.28
b1	0.10	0.15	0.20
c	0.07	0.12	0.17
D	0.75	0.80	0.85
E	0.55	0.60	0.65
e	0.35	0.38	0.40
H	0.950	1.000	1.050
L	0.185 REF		
L2	0.05	0.10	0.15


**RECOMMENDED
MOUNTING FOOTPRINT**

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. N/C
3. Cathode

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P	PAGE 1 OF 1

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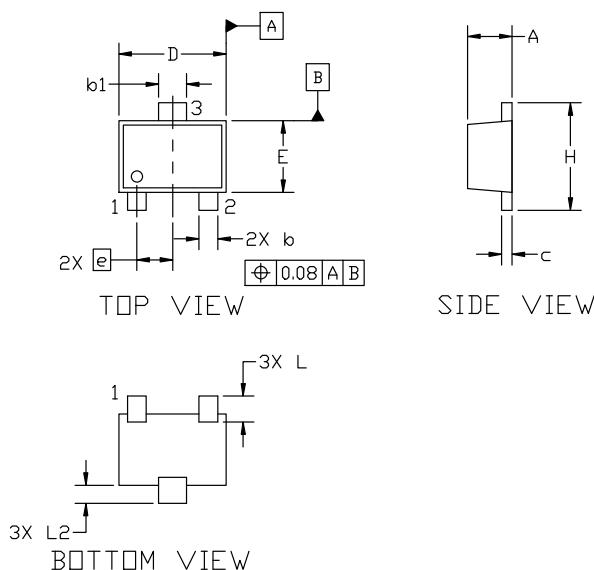


SOT-723 1.20x0.80x0.50, 0.40P
CASE 631AA
ISSUE E

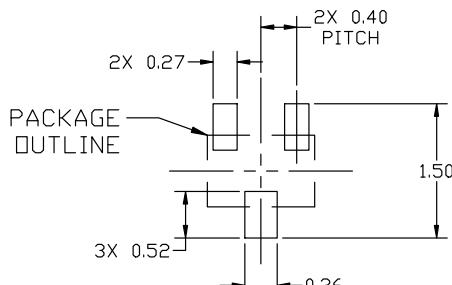
DATE 24 JAN 2024

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



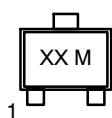
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
c	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25



RECOMMENDED MOUNTING
FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. Emitter
3. Collector

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

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